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(54) METHOD FOR FORMING SHIELD TUNNELS IN SINGLE-CRYSTAL SUBSTRATES

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(58) Field of Classification Search

None

See application file for complete search history.

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(57) ABSTRACT

A method of processing a single-crystal member includes setting the peak energy density of a pulsed laser beam to a value in a range from 1 TW/cm² to 100 TW/cm², and applying the pulsed laser beam to the single-crystal member while positioning a converged point of the pulsed laser beam at a predetermined position spaced from an upper side of the single-crystal member to grow a fine hole and a amorphous region shielding the fine hole from the upper side of the single-crystal member, thereby forming a shield tunnel in the single-crystal member.

2 Claims, 7 Drawing Sheets

